Lan Fu

List of Publications by Year
in descending order

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215	4,807	81743 39	118652 62
papers	citations	h-index	g-index

218	218	218	5335
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Broadband Metamaterial Absorbers. Advanced Optical Materials, 2019, 7, 1800995.	3.6	404
2	Ultraporous Electronâ€Depleted ZnO Nanoparticle Networks for Highly Sensitive Portable Visibleâ€Blind UV Photodetectors. Advanced Materials, 2015, 27, 4336-4343.	11.1	222
3	Selective-Area Epitaxy of Pure Wurtzite InP Nanowires: High Quantum Efficiency and Room-Temperature Lasing. Nano Letters, 2014, 14, 5206-5211.	4.5	198
4	Colossal Dielectric Permittivity in (Nb+Al) Codoped Rutile TiO₂ Ceramics: Compositional Gradient and Local Structure. Chemistry of Materials, 2015, 27, 4934-4942.	3.2	189
5	Bidirectional photocurrent in pâ€“n heterojunction nanowires. Nature Electronics, 2021, 4, 645-652.	13.1	129
6	Water Droplet Motion Control on Superhydrophobic Surfaces: Exploiting the Wenzel-to-Cassie Transition. Langmuir, 2011, 27, 2595-2600.	1.6	118
7	Single Nanowire Photoconductive Terahertz Detectors. Nano Letters, 2015, 15, 206-210.	4.5	105
8	Influence of surface passivation on ultrafast carrier dynamics and terahertz radiation generation in GaAs. Applied Physics Letters, 2006, 89, 232102.	1.5	103
9	Extraordinarily Bound Quasi-One-Dimensional Trions in Two-Dimensional Phosphorene Atomic Semiconductors. ACS Nano, 2016, 10, 2046-2053.	7.3	92
10	Three-dimensional nano-heterojunction networks: a highly performing structure for fast visible-blind UV photodetectors. Nanoscale, 2017, 9, 2059-2067.	2.8	82
11	Three-dimensional cross-nanowire networks recover full terahertz state. Science, 2020, 368, 510-513.	6.0	81
12	IIIâ€“V Semiconductor Single Nanowire Solar Cells: A Review. Advanced Materials Technologies, 2018, 3, 1800005.	3.0	75
13	Tunable Polarity in a IIIâ€“V Nanowire by Droplet Wetting and Surface Energy Engineering. Advanced Materials, 2015, 27, 6096-6103.	11.1	69
14	Doping-enhanced radiative efficiency enables lasing in unpassivated GaAs nanowires. Nature Communications, 2016, 7, 11927.	5.8	68
15	Liquidâ€Metal Synthesized Ultrathin SnS Layers for Highâ€Performance Broadband Photodetectors. Advanced Materials, 2020, 32, e2004247.	11.1	66
16	Room temperature GaAsSb single nanowire infrared photodetectors. Nanotechnology, 2015, 26, 445202.	1.3	63
17	Low-Voltage High-Performance UV Photodetectors: An Interplay between Grain Boundaries and Debye Length. ACS Applied Materials & Interfaces, 2017, 9, 2606-2615.	4.0	62
18	Ferroelectric-Driven Exciton and Trion Modulation in Monolayer Molybdenum and Tungsten Diselenides. ACS Nano, 2019, 13, 5335-5343.	7.3	61

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19	Efficiency enhancement of axial junction InP single nanowire solar cells by dielectric coating. Nano Energy, 2016, 28, 106-114.	8.2	58
20	Suppression of interdiffusion in InGaAs/GaAs quantum dots using dielectric layer of titanium dioxide. Applied Physics Letters, 2003, 82, 2613-2615.	1.5	57
21	Simultaneous Selective-Area and Vaporâ€"Liquidâ€"Solid Growth of InP Nanowire Arrays. Nano Letters, 2016, 16, 4361-4367.	4.5	57
22	High-Efficiency Monolayer Molybdenum Ditelluride Light-Emitting Diode and Photodetector. ACS Applied Materials & Interfaces, 2018, 10, 43291-43298.	4.0	56
23	Electron-hole recombination properties of In0.5Ga0.5As/GaAs quantum dot solar cells and the influence on the open circuit voltage. Applied Physics Letters, 2010, 97, .	1.5	54
24	Photoconductive response correction for detectors of terahertz radiation. Journal of Applied Physics, 2008, 104, .	1.1	53
25	Over 1.0mm-long boron nitride nanotubes. Chemical Physics Letters, 2008, 463, 130-133.	1.2	51
26	Tunable Bandâ€Selective UVâ€Photodetectors by 3D Selfâ€Assembly of Heterogeneous Nanoparticle Networks. Advanced Functional Materials, 2016, 26, 7359-7366.	7.8	50
27	Moleculeâ€Induced Conformational Change in Boron Nitride Nanosheets with Enhanced Surface Adsorption. Advanced Functional Materials, 2016, 26, 8202-8210.	7.8	47
28	An ion-implanted InP receiver for polarization resolved terahertz spectroscopy. Optics Express, 2007, 15, 7047.	1.7	46
29	Broadband Phase-Sensitive Single InP Nanowire Photoconductive Terahertz Detectors. Nano Letters, 2016, 16, 4925-4931.	4.5	46
30	Effects of rapid thermal annealing on device characteristics of InGaAsâˆ•GaAs quantum dot infrared photodetectors. Journal of Applied Physics, 2006, 99, 114517.	1.1	45
31	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. ACS Nano, 2019, 13, 3492-3499.	7.3	45
32	Influence of Electrical Design on Coreâ€"Shell GaAs Nanowire Array Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 854-864.	1.5	44
33	Review on III-V Semiconductor Single Nanowire-Based Room Temperature Infrared Photodetectors. Materials, 2020, 13, 1400.	1.3	44
34	In/sub 0.5/Ga/sub 0.5/As/GaAs quantum dot infrared photodetectors grown by metal-organic chemical vapor deposition. IEEE Electron Device Letters, 2005, 26, 628-630.	2.2	43
35	Spatially Resolved Doping Concentration and Nonradiative Lifetime Profiles in Single Si-Doped InP Nanowires Using Photoluminescence Mapping. Nano Letters, 2015, 15, 3017-3023.	4.5	43
36	Identification and modulation of electronic band structures of single-phase Î²-(AlxGa1âˆ'x)2O3 alloys grown by laser molecular beam epitaxy. Applied Physics Letters, 2018, 113, .	1.5	43

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37	Engineering IIIâ€"V Semiconductor Nanowires for Device Applications. Advanced Materials, 2020, 32, e1904359.	11.1	43
38	Structural Engineering of Nanoâ€Grain Boundaries for Lowâ€Voltage UVâ€Photodetectors with Gigantic Photoâ€•to Darkâ€Current Ratios. Advanced Optical Materials, 2016, 4, 1787-1795.	3.6	42
39	Giant optical pathlength enhancement in plasmonic thin film solar cells using core-shell nanoparticles. Journal Physics D: Applied Physics, 2018, 51, 295106.	1.3	42
40	Three-Dimensional in Situ Photocurrent Mapping for Nanowire Photovoltaics. Nano Letters, 2013, 13, 1405-1409.	4.5	39
41	The role of intersubband optical transitions on the electrical properties of InGaAs/GaAs quantum dot solar cells. Progress in Photovoltaics: Research and Applications, 2013, 21, 736-746.	4.4	38
42	Observation of polarity-switchable photoconductivity in III-nitride/MoSx core-shell nanowires. Light: Science and Applications, 2022, 11, .	7.7	38
43	Influence of rapid thermal annealing on a 30 stack InAs/GaAs quantum dot infrared photodetector. Journal of Applied Physics, 2003, 94, 5283.	1.1	37
44	Temperature dependence of dark current properties of InGaAs/GaAs quantum dot solar cells. Applied Physics Letters, 2011, 98, .	1.5	36
45	Broadband GaAsSb Nanowire Array Photodetectors for Filter-Free Multispectral Imaging. Nano Letters, 2021, 21, 7388-7395.	4.5	36
46	Suppression of interdiffusion in GaAs/AlGaAs quantum-well structure capped with dielectric films by deposition of gallium oxide. Journal of Applied Physics, 2002, 92, 3579-3583.	1.1	35
47	Two-dimensional materials for light emitting applications: Achievement, challenge and future perspectives. Nano Research, 2021, 14, 1912-1936.	5.8	34
48	Improvement of the kink-free operation in ridge-waveguide laser diodes due to coupling of the optical field to the metal layers outside the ridge. IEEE Photonics Technology Letters, 2003, 15, 1686-1688.	1.3	33
49	Vertically Emitting Indium Phosphide Nanowire Lasers. Nano Letters, 2018, 18, 3414-3420.	4.5	33
50	Multiwavelength Single Nanowire InGaAs/InP Quantum Well Light-Emitting Diodes. Nano Letters, 2019, 19, 3821-3829.	4.5	32
51	Improved Performance of GaAs-Based Terahertz Emitters via Surface Passivation and Silicon Nitride Encapsulation. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 17-21.	1.9	31
52	Large-Scale Statistics for Threshold Optimization of Optically Pumped Nanowire Lasers. Nano Letters, 2017, 17, 4860-4865.	4.5	31
53	High-Efficiency Solar Cells from Extremely Low Minority Carrier Lifetime Substrates Using Radial Junction Nanowire Architecture. ACS Nano, 2019, 13, 12015-12023.	7.3	31
54	Design Principles for Fabrication of InP-Based Radial Junction Nanowire Solar Cells Using an Electron Selective Contact. IEEE Journal of Photovoltaics, 2019, 9, 980-991.	1.5	31

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55	Nano Au-decorated boron nitride nanotubes: Conductance modification and field-emission enhancement. Applied Physics Letters, 2008, 92, 243105.	1.5	30
56	A plasmonic staircase nano-antenna device with strong electric field enhancement for surface enhanced Raman scattering (SERS) applications. Journal Physics D: Applied Physics, 2012, 45, 305102.	1.3	30
57	Proton irradiation-induced intermixing in InGaAs/(Al)GaAs quantum wells and quantum-well lasers. Journal of Applied Physics, 1999, 85, 6786-6789.	1.1	29
58	Doping effect on dark currents in In0.5Ga0.5Asâˆ•GaAs quantum dot infrared photodetectors grown by metal-organic chemical vapor deposition. Applied Physics Letters, 2006, 89, 113510.	1.5	29
59	Indium phosphide based solar cell using ultra-thin ZnO as an electron selective layer. Journal Physics D: Applied Physics, 2018, 51, 395301.	1.3	28
60	Improved carrier collection in intermixed InGaAs/GaAs quantum wells. Applied Physics Letters, 1998, 73, 3408-3410.	1.5	26
61	Effects of well thickness on the spectral properties of In0.5Ga0.5Asâˆ•GaAsâˆ•Al0.2Ga0.8As quantum dots-in-a-well infrared photodetectors. Applied Physics Letters, 2008, 92, 193507.	1.5	26
62	Plasmonic quantum dot solar cells for enhanced infrared response. Applied Physics Letters, 2012, 100, .	1.5	26
63	Single n⁺-i-n⁺InP nanowires for highly sensitive terahertz detection. Nanotechnology, 2017, 28, 125202.	1.3	26
64	Radial Growth Evolution of InGaAs/InP Multi-Quantum-Well Nanowires Grown by Selective-Area Metal Organic Vapor-Phase Epitaxy. ACS Nano, 2018, 12, 10374-10382.	7.3	26
65	Quality of silica capping layer and its influence on quantum-well intermixing. Applied Physics Letters, 2000, 76, 837-839.	1.5	23
66	Reducing Zn diffusion in single axial junction InP nanowire solar cells for improved performance. Progress in Natural Science: Materials International, 2018, 28, 178-182.	1.8	23
67	Highly uniform InGaAs/InP quantum well nanowire array-based light emitting diodes. Nano Energy, 2020, 71, 104576.	8.2	23
68	Nanowire Quantum Dot Surface Engineering for High Temperature Single Photon Emission. ACS Nano, 2019, 13, 13492-13500.	7.3	22
69	Axial pâ€n junction design and characterization for InP nanowire array solar cells. Progress in Photovoltaics: Research and Applications, 2019, 27, 237-244.	4.4	22
70	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications. Advanced Functional Materials, 2022, 32, 2103057.	7.8	21
71	Interdiffused quantum-well infrared photodetectors for color sensitive arrays. Applied Physics Letters, 1999, 75, 923-925.	1.5	20
72	Influence of quantum well and barrier composition on the spectral behavior of InGaAs quantum dots-in-a-well infrared photodetectors. Applied Physics Letters, 2007, 91, 173508.	1.5	19

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73	Ultralow Threshold, Single-Mode InGaAs/GaAs Multiquantum Disk Nanowire Lasers. ACS Nano, 2021, 15, 9126-9133.	7.3	19
74	Tuning the detection wavelength of quantum-well infrared photodetectors by single high-energy implantation. Applied Physics Letters, 2001, 78, 10-12.	1.5	18
75	Unexpected benefits of stacking faults on the electronic structure and optical emission in wurtzite GaAs/GaInP core/shell nanowires. Nanoscale, 2019, 11, 9207-9215.	2.8	18
76	Design of Ultrathin InP Solar Cell Using Carrier Selective Contacts. IEEE Journal of Photovoltaics, 2020, 10, 1657-1666.	1.5	18
77	Selfâ€Powered InP Nanowire Photodetector for Singleâ€Photon Level Detection at Room Temperature. Advanced Materials, 2021, 33, e2105729.	11.1	18
78	Study of intermixing in a GaAs/AlGaAs quantum-well structure using doped spin-on silica layers. Applied Physics Letters, 2002, 80, 1171-1173.	1.5	16
79	Single nanowire green InGaN/GaN light emitting diodes. Nanotechnology, 2016, 27, 435205.	1.3	16
80	Direct observation and manipulation of hot electrons at room temperature. National Science Review, 2021, 8, nwaa295.	4.6	16
81	Semiconductor Nanowire Arrays for Highâ€Performance Miniaturized Chemical Sensing. Advanced Functional Materials, 2022, 32, 2107596.	7.8	16
82	Impurity-free disordering of InAsâˆ•InP quantum dots. Applied Physics Letters, 2007, 90, 243114.	1.5	15
83	Two-color InGaAsâˆ•GaAs quantum dot infrared photodetectors by selective area interdiffusion. Applied Physics Letters, 2008, 93, 013504.	1.5	15
84	Slowing Hot-Electron Relaxation in Mix-Phase Nanowires for Hot-Carrier Photovoltaics. Nano Letters, 2021, 21, 7761-7768.	4.5	15
85	Impurity-free disordering mechanisms in GaAs-based structures using doped spin-on silica layers. Applied Physics Letters, 2002, 80, 4351-4353.	1.5	14
86	Influence of SiO2and TiO2dielectric layers on the atomic intermixing of InxGa1âˆ'xAs/InP quantum well structures. Semiconductor Science and Technology, 2007, 22, 988-992.	1.0	14
87	Radiation effects on GaAs/AlGaAs core/shell ensemble nanowires and nanowire infrared photodetectors. Nanotechnology, 2017, 28, 125702.	1.3	14
88	Light-Induced Positive and Negative Photoconductances of InAs Nanowires toward Rewritable Nonvolatile Memory. ACS Applied Electronic Materials, 2019, 1, 1825-1831.	2.0	14
89	Large area van der Waals epitaxy of IIâ€"VI CdSe thin films for flexible optoelectronics and full-color imaging. Nano Research, 2022, 15, 368-376.	5.8	14
90	Merging Photonic Wire Lasers and Nanoantennas. Journal of Lightwave Technology, 2011, 29, 2690-2697.	2.7	13

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91	The conduction band absorption spectrum of interdiffused InGaAs/GaAs quantum dot infrared photodetectors. Journal of Applied Physics, 2012, 111, .	1.1	13
92	Integration of bandpass guided-mode resonance filters with mid-wavelength infrared photodetectors. Journal Physics D: Applied Physics, 2013, 46, 095104.	1.3	13
93	In situ passivation of GaAsSb nanowires for enhanced infrared photoresponse. Nanotechnology, 2020, 31, 244002.	1.3	13
94	Self-frequency-conversion nanowire lasers. Light: Science and Applications, 2022, 11, 120.	7.7	13
95	Enhanced Contactless Salt-Collecting Solar Desalination. ACS Applied Materials & Interfaces, 2022, 14, 34151-34158.	4.0	13
96	Proton implantation and rapid thermal annealing effects on GaAs/AlGaAs quantum well infrared photodetectors. Superlattices and Microstructures, 1999, 26, 317-324.	1.4	12
97	Suppression of thermal atomic interdiffusion in C-doped InGaAsâˆ•AlGaAs quantum well laser structures using TiO2 dielectric layers. Applied Physics Letters, 2004, 85, 5583-5585.	1.5	12
98	Study of intermixing in InGaAsâˆ•(Al)GaAs quantum well and quantum dot structures for optoelectronicâˆ•photonic integration. IET Circuits, Devices and Systems, 2005, 152, 491.	0.6	12
99	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. Scientific Reports, 2017, 7, 7503.	1.6	12
100	Effects of Zn Doping on Intermixing in InGaAs/AlGaAs Laser Diode Structures. Journal of the Electrochemical Society, 2003, 150, G481.	1.3	10
101	Investigations of impurity-free vacancy disordering in (Al)InGaAs(P)/InGaAs quantum wells. Semiconductor Science and Technology, 2010, 25, 055014.	1.0	10
102	Periodic dielectric structures for light-trapping in InGaAs/GaAs quantum well solar cells. Optics Express, 2013, 21, A324.	1.7	10
103	Enhanced carrier collection efficiency and reduced quantum state absorption by electron doping in self-assembled quantum dot solar cells. Applied Physics Letters, 2015, 106, .	1.5	10
104	A Highâ€Efficiency Wavelengthâ€Tunable Monolayer LED with Hybrid Continuousâ€Pulsed Injection. Advanced Materials, 2021, 33, e2101375.	11.1	10
105	Multiple Wavelength InGaAs Quantum Dot Lasers Using Ion Implantation Induced Intermixing. Nanoscale Research Letters, 2007, 2, 550-553.	3.1	9
106	Single-mode operation of a large optically pumped triangular laser with lateral air trenches. Journal of the Optical Society of America B: Optical Physics, 2009, 26, 1417.	0.9	8
107	Enhancement of radiation tolerance in GaAs/AlGaAs coreâ€“shell and InP nanowires. Nanotechnology, 2018, 29, 225703.	1.3	8
108	Modal refractive index measurement in nanowire lasersâ€”a correlative approach. Nano Futures, 2018, 2, 035004.	1.0	8

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109	Flexible InPâ€"ZnO nanowire heterojunction light emitting diodes. Nanoscale Horizons, 2022, 7, 446-454.	4.1	8
110	Effects of thermal stress on interdiffusion in InGaAsN/GaAs quantum dots. Applied Physics Letters, 2004, 84, 4950-4952.	1.5	7
111	Properties of In0.5Ga0.5As/GaAs/Al0.2Ga0.8As quantum-dots-in-a-well infrared photodetectors. Journal Physics D: Applied Physics, 2009, 42, 095101.	1.3	7
112	Selective Intermixing of InGaAs/GaAs Quantum Dot Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2011, 47, 577-590.	1.0	7
113	Intermixing of InGaAs/GaAs quantum wells and quantum dots using sputter-deposited silicon oxynitride capping layers. Journal of Applied Physics, 2012, 112, .	1.1	7
114	Tuning of detection wavelength of quantum-well infrared photodetectors by quantum-well intermixing. Infrared Physics and Technology, 2001, 42, 171-175.	1.3	6
115	Quantum Dots and Nanowires Grown by Metalâ€"Organic Chemical Vapor Deposition for Optoelectronic Device Applications. IEEE Transactions on Energy Conversion, 2006, 12, 1242-1254.	3.7	6
116	Effects of annealing on the spectral response and dark current of quantum dot infrared photodetectors. Journal Physics D: Applied Physics, 2008, 41, 215101.	1.3	6
117	Investigation of ion implantation induced intermixing in InP based quaternary quantum wells. Journal Physics D: Applied Physics, 2011, 44, 475105.	1.3	6
118	Investigation of lightâ€"matter interaction in single vertical nanowires in ordered nanowire arrays. Nanoscale, 2022, 14, 3527-3536.	2.8	6
119	Design of InAs nanosheet arrays with ultrawide polarization-independent high absorption for infrared photodetection. Applied Physics Letters, 2022, 120, .	1.5	6
120	Proton irradiation-induced intermixing in InxGa1â^'xAs/InP quantum wellsâ€"the effect of In composition. Semiconductor Science and Technology, 2006, 21, 1441-1446.	1.0	5
121	Recombination properties of Si-doped InGaAs/GaAs quantum dots. Nanotechnology, 2006, 17, 5373-5377.	1.3	5
122	Effect of GaP strain compensation layers on rapid thermally annealed InGaAsâ^•GaAs quantum dot infrared photodetectors grown by metal-organic chemical-vapor deposition. Applied Physics Letters, 2007, 91, .	1.5	5
123	Increasing the coupling efficiency of a microdisk laser to waveguides by using well designed spiral structures. Journal of Applied Physics, 2010, 107, 043105.	1.1	5
124	The influence of doping on the device characteristics of In0.5Ga0.5As/GaAs/Al0.2Ga0.8As quantum dots-in-a-well infrared photodetectors. Nanoscale, 2010, 2, 1128.	2.8	5
125	Damage analysis of a perfect broadband absorber by a femtosecond laser. Scientific Reports, 2019, 9, 15880.	1.6	5
126	Impurity-free vacancy disordering of quantum heterostructures with SiOxNy encapsulants deposited by magnetron sputtering. , 2008, , .		4

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127	Spatially resolved characterization of InGaAs/GaAs quantum dot structures by scanning spreading resistance microscopy. Applied Physics Letters, 2010, 97, 041106.	1.5	4
128	Reply to Comment on Water Droplet Motion Control on Superhydrophobic Surfaces: Exploiting the Wenzel-to-Cassie Transition. Langmuir, 2011, 27, 13962-13963.	1.6	4
129	Nanowire solar cells for next-generation photovoltaics. SPIE Newsroom, 0, , .	0.1	4
130	High Fluence Chromium and Tungsten Bowtie Nano-antennas. Scientific Reports, 2019, 9, 13023.	1.6	4
131	Electron selective contact for high efficiency core-shell nanowire solar cell. , 2019, , .		4
132	The asymmetry in the characteristics of GaAs/AlGaAs quantum well infrared photodetectors. Journal of Crystal Growth, 2001, 222, 786-790.	0.7	3
133	The use of strain compensation layers in the growth of stacked quantum dot structures. , 0, , .		3
134	Coupling Analysis of GaAs-Based Microdisk Lasers With Different External Claddings. Journal of Lightwave Technology, 2009, 27, 5090-5098.	2.7	3
135	Merged beam laser design for reduction of gain-saturation and two-photon absorption in high power single mode semiconductor lasers. Optics Express, 2013, 21, 8276.	1.7	3
136	Comparison of interdiffusion between single and stacked-layer InGaAs/GaAs quantum dots. , 0, , .		2
137	Photonic crystal-enhanced quantum dot infrared photodetectors. , 2008, , .		2
138	Thermal expansion coefficients and composition of sputter-deposited silicon oxynitride thin films. Journal Physics D: Applied Physics, 2010, 43, 335104.	1.3	2
139	Broadband Photodetectors: Liquidâ€Metal Synthesized Ultrathin SnS Layers for Highâ€Performance Broadband Photodetectors (Adv. Mater. 45/2020). Advanced Materials, 2020, 32, 2070338.	11.1	2
140	Effect of dopants in the spin-on glass layer on the bandgap shift in GaAs/AlGaAs and InGaAs/AlGaAs intermixed quantum wells. , 0, , .		1
141	Quantum well intermixing for optoelectronic device integration. , 0, , .		1
142	Rapid thermal annealing study of InGaAs/GaAs quantum dot infrared photodetectors grown by metal-organic chemical vapor deposition. , 2005, , .		1
143	Quantum dots-in-a-well infrared photodetectors grown by MOCVD. , 2006, , .		1
144	Thermal Annealing Study On InGaAs/GaAs Quantum Dot Infrared Photodetectors. , 2006, , .		1

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145	Analytical expression for the quantum dot contribution to the quasistatic capacitance for conduction band characterization. Journal of Applied Physics, 2008, 104, 023713.	1.1	1
146	Spectral tuning of InGaAs/GaAs quantum dot infrared photodetectors using selective-area intermixing. , 2010, , .		1
147	InP nanowires grown by SA-MOVPE. , 2012, , .		1
148	Improved GaAs nanowire solar cells using AlGaAs for surface passivation. , 2012, , .		1
149	Improved performance of InGaAs/GaAs quantum dot solar cells using Si-modulation doping. , 2012, , .		1
150	A study of quantum well solar cell structures with bound-to-continuum transitions for reduced carrier recombination. Applied Physics Letters, 2013, 102, 213903.	1.5	1
151	Measurement of doping concentration, internal quantum efficiency and non-radiative lifetime of InP nanowires. , 2014, , .		1
152	Selective area epitaxial growth of InP nanowire array for solar cell applications. , 2014, , .		1
153	Single GaAs/AlGaAs nanowire photoconductive terahertz detectors. , 2014, , .		1
154	Single Nanowire Terahertz Detectors. , 2015, , .		1
155	2D Nanomaterials: Moleculeâ€Induced Conformational Change in Boron Nitride Nanosheets with Enhanced Surface Adsorption (Adv. Funct. Mater. 45/2016). Advanced Functional Materials, 2016, 26, 8356-8356.	7.8	1
156	Room Temperature GaAsSb Array Photodetectors. , 2018, , .		1
157	Distinguishing cap and core contributions to the photoconductive terahertz response of single GaAs based coreâ€“shellâ€“cap nanowire detectors. Lithuanian Journal of Physics, 2018, 58, .	0.1	1
158	Direct Characterization of Axial p-n Junctions for InP Nanowire Array Solar Cells Using Electron Beam-Induced Current. , 2015, , .		1
159	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications (Adv. Funct. Mater. 3/2022). Advanced Functional Materials, 2022, 32, .	7.8	1
160	Multiple energy proton implantation induced quantum well intermixing in GaAs/AlGaAs quantum-well infrared photodetectors. , 0, , .		0
161	Intermixing effect in quantum well infrared detector. , 2000, 4130, 348.		0
162	Thermoluminescence in GaAs. , 0, , .		0

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163	Postgrowth wavelength tuning of optoelectronic devices by ion implantation induced quantum well intermixing. , 0, , .		0
164	High power, kink-free 970 nm InGaAs/AlGaAs laser diodes with asymmetric structure. , 0, , .		0
165	<title>Use of ion implantation for the creation of ultrafast photodetector materials and tuning of quantum well infrared photodetectors</title>. , 2001, , .		0
166	Possibility of improved frequency response from intermixed quantum-well devices. Superlattices and Microstructures, 2001, 29, 105-110.	1.4	0
167	Suppression of interdiffusion in In/sub 0.5/Ga/sub 0.5/As/GaAs quantum dots. , 0, , .		0
168	Strain relaxation in rapid thermally annealed InAs/GaAs quantum dot infrared photodetectors. , 0, , .		0
169	Improvement of kink-free operation in InGaAs/GaAs/AlGaAs high power, ridge waveguide laser diodes. , 0, , .		0
170	Spatial selectivity of impurity free vacancy disordering using different dielectric layers for photonic/optoelectronic integrated circuits. , 0, , .		0
171	Impurity-free vacancy disordering of quantum wells and quantum dots for optoelectronic/photonic integrated circuits. , 2004, , .		0
172	Suppression of thermal atomic interdiffusion in InGaAs/AlGaAs QW laser structures. , 2004, , .		0
173	Toward quantum-dot-based photonic integrated circuits. , 2005, 5729, 41.		0
174	Compound semiconductor optoelectronics research at the Australian National University. , 2005, , .		0
175	InGaAs quantum dots-in-a-well photodetectors grown by metal organic chemical vapor deposition. , 2005, , .		0
176	Carrier transfer and magneto-transport in single modulation-doped V-grooved quantum wire modified by ion implantation. Journal of Luminescence, 2006, 119-120, 198-203.	1.5	0
177	Micro-Photoluminescence Confocal Mapping of Single V-Grooved GaAs Quantum Wire. Chinese Physics Letters, 2006, 23, 3341-3344.	1.3	0
178	THz Emitters and Detectors Based on Ion Implanted III-V Semiconductors. , 2006, , .		0
179	Spectral behavior of quantum dots-in-a-well infrared photodetectors grown by MOCVD. , 2007, , .		0
180	Role of stress on impurity free disordering of quantu m dots. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0

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